

IN THE CLAIMS

Please amend the claims as follows:

1. (Original) A semiconductor device comprising:

a bulk region formed in a semiconductor substrate; and

a semiconductor region formed on one of a buried insulating film in said semiconductor substrate and a cavity region formed in said semiconductor substrate; said bulk region including:

a memory cell array having a plurality of memory cells arranged in the form of a matrix and including a plurality of memory cells connected to bit lines and word lines;

sense amplifier connected to said bit lines of said memory cell array, said sense amplifier being adapted to sense and amplify the potentials of said bit lines; and

column selection gate for connecting said sense amplifier to first data line;

said semiconductor region including:

word line selection circuit for selecting appropriate ones of said word lines; and

column selection circuit for selecting appropriate ones of said column selection gate.

2-32. (Canceled)